

IRHNJ9130 (JANSR2N7382U3)

PD-94277B

Radiation Hardened Power MOSFET

Surface Mount (SMD-0.5)

100V, -11A, P-channel, Rad Hard HEXFET™ Technology

Features

- Single event effect (SEE) hardened
- Low $R_{DS(on)}$
- Low total gate charge
- Simple drive requirements
- Hermetically sealed
- Light weight
- Surface Mount
- ESD rating: Class 1B per MIL-STD-750, Method 1020

Potential Applications

- DC-DC converter
- Motor drives
- Thermal management

Product Validation

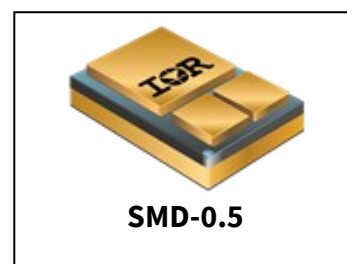
Qualified to JANS screening flow according to MIL-PRF-19500 for space applications

Description

IR HiRel rad hard HEXFET technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low $R_{DS(on)}$ and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well-established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Product Summary

- BV_{DSS} : -100V
- I_D : -11A
- $R_{DS(on),max}$: 0.29Ω
- $Q_{G,max}$: 45nC
- REF: MIL-PRF-19500/615



Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level	TID Level
IRHNJ9130	SMD-0.5	COTS	100 krad(Si)
JANSR2N7382U3	SMD-0.5	JANS	100 krad(Si)
IRHNJ9130SCS	SMD-0.5	S-Level	100 krad(Si)
IRHNJ9130SCV	SMD-0.5	JANTXV-equivalent	100 krad(Si)
IRHNJ93130	SMD-0.5	COTS	300 krad(Si)
JANSF2N7382U3	SMD-0.5	JANS	300 krad(Si)
IRHNJ93130SCS	SMD-0.5	S-Level	300 krad(Si)
IRHNJ93130SCV	SMD-0.5	JANTXV-equivalent	300 krad(Si)

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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
$I_{D1} @ V_{GS} = -12V, T_C = 25^{\circ}C$	Continuous Drain Current	-11	A
$I_{D2} @ V_{GS} = -12V, T_C = 100^{\circ}C$	Continuous Drain Current	-7.0	A
$I_{DM} @ T_C = 25^{\circ}C$	Pulsed Drain Current ¹	-44	A
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	75	W
	Linear Derating Factor	0.6	W/ $^{\circ}C$
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ²	150	mJ
I_{AR}	Avalanche Current ¹	-11	A
E_{AR}	Repetitive Avalanche Energy ¹	7.5	mJ
dv/dt	Peak Diode Reverse Recovery ³	-16	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$
	Lead Temperature	300 (for 5 sec)	
	Weight	1.0 (Typical)	

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.² $V_{DD} = -25V$, starting $T_J = 25^{\circ}C$, $L = 2.4mH$, Peak $I_L = -11A$, $V_{GS} = -12V$ ³ $I_{SD} \leq -11A$, $di/dt \leq -440A/\mu s$, $V_{DD} \leq -100V$, $T_J \leq 150^{\circ}C$

Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics (Pre-Irradiation)

Table 3 Static and Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V, I_D = -1.0mA$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1.0mA$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.29	Ω	$V_{GS} = -12V, I_{D2} = -7.0A^1$
		—	—	0.34		$V_{GS} = -12V, I_{D2} = -11A^1$
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -1.0mA$
G_{fs}	Forward Transconductance	2.5	—	—	S	$V_{DS} = -15V, I_{D2} = -7.0A^1$
I_{DSS}	Zero Gate Voltage Drain Current	—	—	-25	μA	$V_{DS} = -80V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Leakage Reverse	—	—	100		$V_{GS} = 20V$
Q_G	Total Gate Charge	—	—	45	nC	$I_{D1} = -11A$
Q_{GS}	Gate-to-Source Charge	—	—	10		$V_{DS} = -50V$
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	25		$V_{GS} = -12V$
$t_{d(on)}$	Turn-On Delay Time	—	—	30	ns	$I_{D1} = -11A^{**}$ $V_{DD} = -50V$ $R_G = 7.5\Omega$ $V_{GS} = -12V$
t_r	Rise Time	—	—	50		
$t_{d(off)}$	Turn-Off Delay Time	—	—	70		
t_f	Fall Time	—	—	70		
$L_s + L_D$	Total Inductance	—	4.0	—	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	—	1200	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	310	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	80	—		$f = 1.0MHz$

** Switching speed maximum limits are based on manufacturing test equipment and capability.

¹ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$

Device Characteristics

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-11	A	
I _{SM}	Pulsed Source Current (Body Diode) ¹	—	—	-44	A	
V _{SD}	Diode Forward Voltage	—	—	-3.0	V	T _J = 25°C, I _S = -11A, V _{GS} = 0V ²
t _{rr}	Reverse Recovery Time	—	—	250	ns	T _J = 25°C, I _F = -11A, V _{DD} ≤ -25V di/dt = -100A/μs ²
Q _{rr}	Reverse Recovery Charge	—	1.0	—	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	1.67	$^\circ\text{C}/\text{W}$
$R_{\theta PCB}$	Junction-to-PC Board	—	12	—	

2.4 Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 3 and 4) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

2.4.1 Electrical Characteristics — Post Total Dose Irradiation

Table 6 Electrical Characteristics @ $T_J = 25^\circ\text{C}$, Post Total Dose Irradiation ^{3, 4}

Symbol	Parameter	100 krad (Si) ⁵		Up to 300 krad (Si) ⁶		Unit	Test Conditions
		Min.	Max.	Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	-100	—	-100	—	V	$V_{GS} = 0\text{V}$, $I_D = -1.0\text{mA}$
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	-4.0	-2.0	-5.0	V	$V_{DS} = V_{GS}$, $I_D = -1.0\text{mA}$
I_{GSS}	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	$V_{GS} = -20\text{V}$
	Gate-to-Source Leakage Reverse	—	100	—	100		$V_{GS} = 20\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	—	-25	—	-25	μA	$V_{DS} = -80\text{V}$, $V_{GS} = 0\text{V}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-3) ²	—	0.3	—	0.3	Ω	$V_{GS} = -12\text{V}$, $I_{D2} = -7.0\text{A}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (SMD-0.5) ²	—	0.29	—	0.29	Ω	$V_{GS} = -12\text{V}$, $I_{D2} = -7.0\text{A}$
V_{SD}	Diode Forward Voltage	—	-3.0	—	-3.0	V	$V_{GS} = 0\text{V}$, $I_F = -11\text{A}$

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.

² Pulse width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2\%$

³ Total Dose Irradiation with V_{GS} Bias. $V_{GS} = -12\text{V}$ applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁴ Total Dose Irradiation with V_{DS} Bias. $V_{DS} = -80\text{V}$ applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁵ Part numbers IRHNJ9130 (JANSR2N7382U3)

⁶ Part numbers IRHNJ93130 (JANSF2N7382U3)

IRHNJ9130 (JANSR2N7382U3)

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Device Characteristics

2.4.2 Single Event Effects — Safe Operating Area

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. 1 and Table 7.

Table 7 Typical Single Event Effects Safe Operating Area

Ion	LET (MeV·cm ² /mg)	Energy (MeV)	Range (μm)	V _{DS} (V)				
				V _{GS} = 0V	V _{GS} = 5V	V _{GS} = 10V	V _{GS} = 15V	V _{GS} = 20V
Cu	28	285	43	-100	-100	-100	-70	-50
Kr	38.8	320	39.6	-100	-100	-75	-50	—
Xe	63.4	348	32.5	-50	—	—	—	—

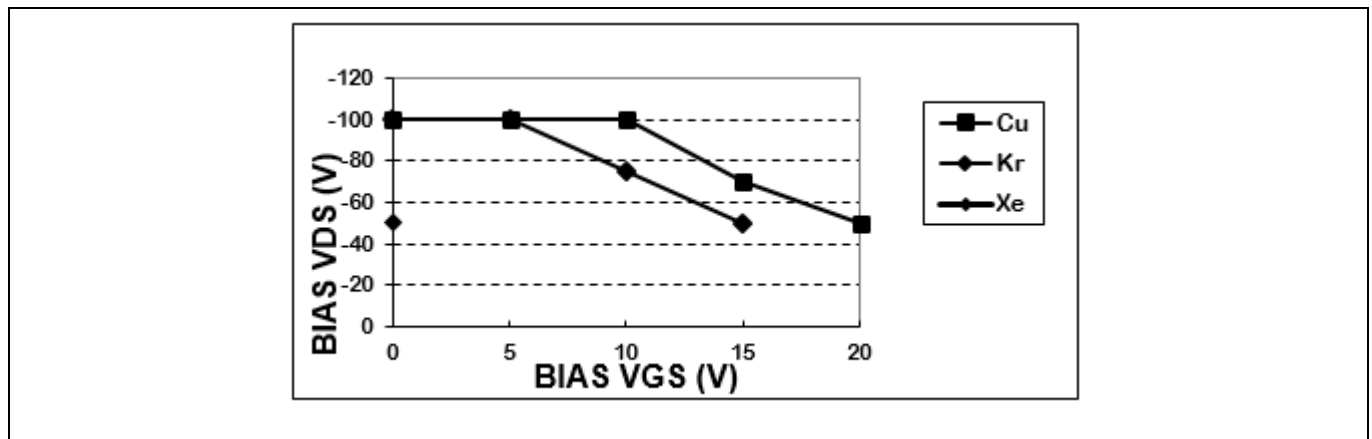


Figure 1 Typical Single Event Effect, Safe Operating Area

IRHNJ9130 (JANSR2N7382U3)

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Electrical Characteristics Curves (Pre-irradiation)

3 Electrical Characteristics Curves (Pre-irradiation)

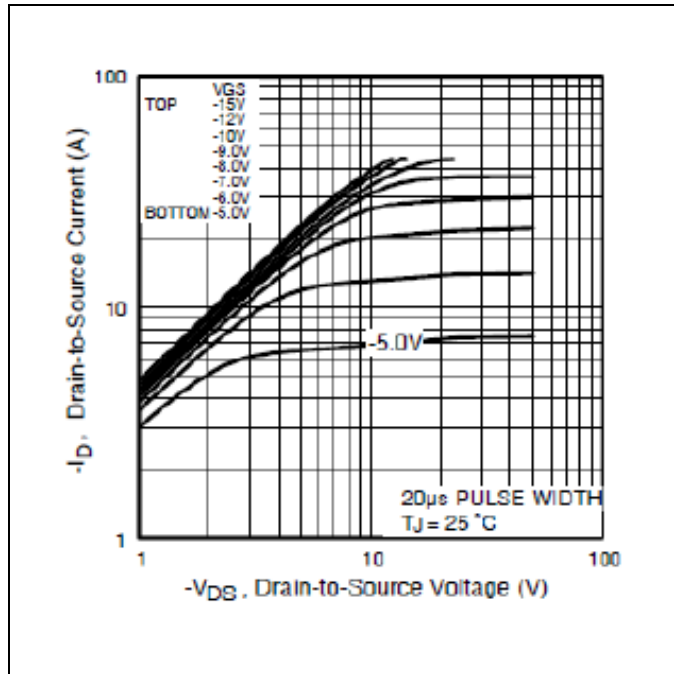


Figure 2 Typical Output Characteristics

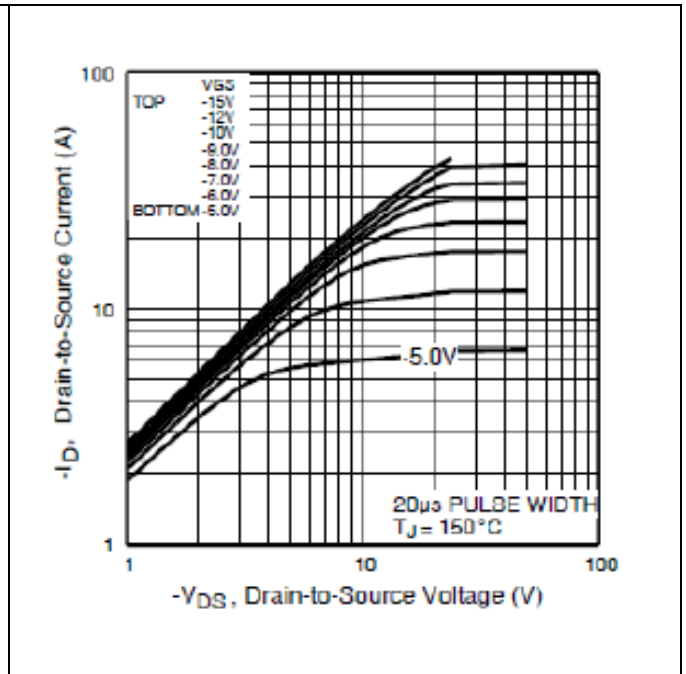


Figure 3 Typical Output Characteristics

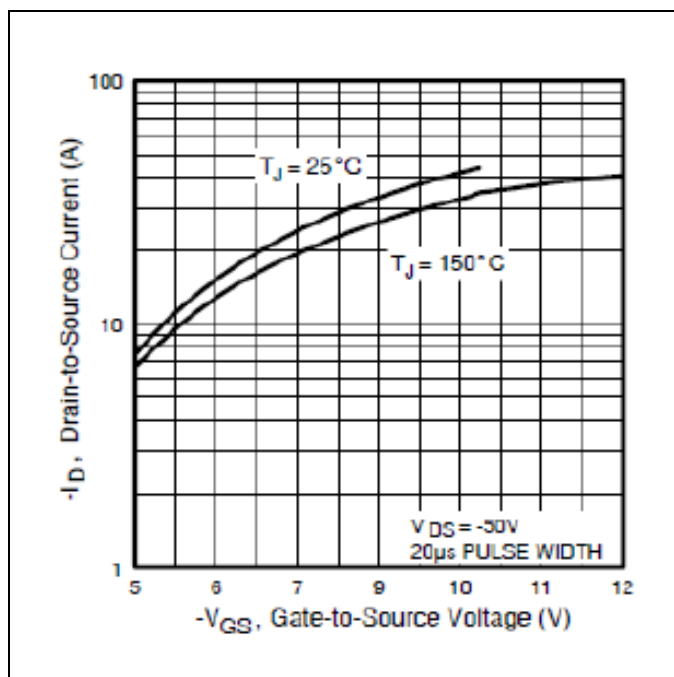


Figure 4 Typical Transfer Characteristics

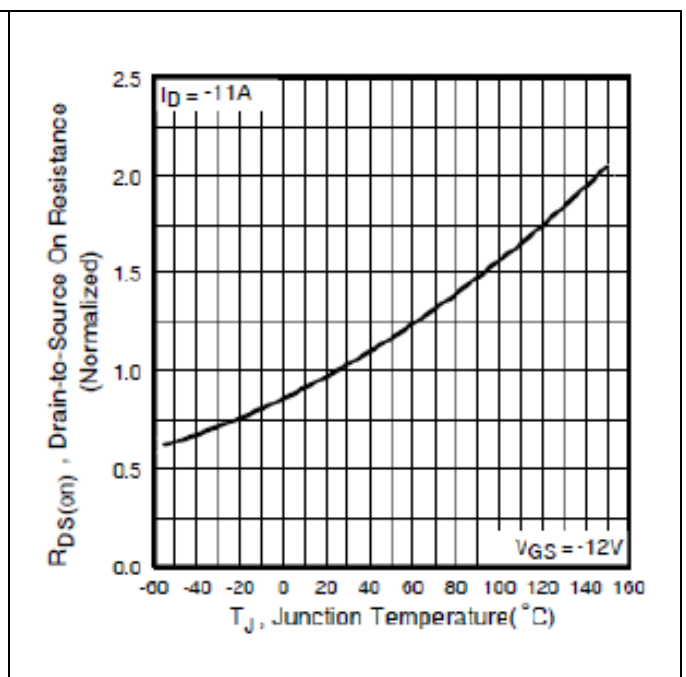


Figure 5 Normalized On-Resistance Vs. Temperature

IRHNJ9130 (JANSR2N7382U3)

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Electrical Characteristics Curves (Pre-irradiation)

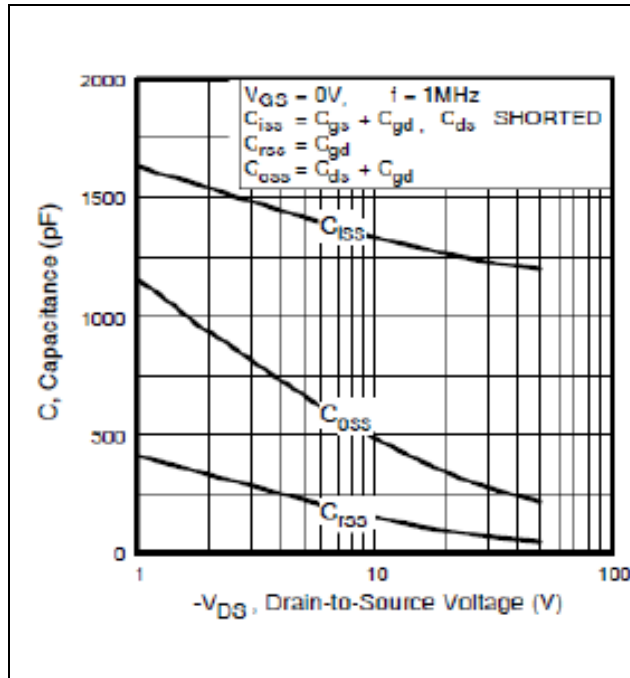


Figure 6 Typical Capacitance Vs. Drain-to-Source Voltage

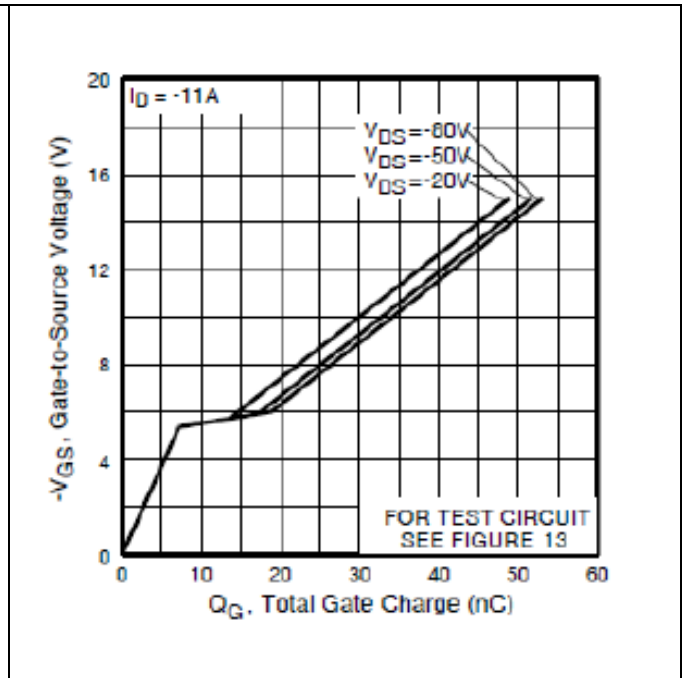


Figure 7 Typical Gate-to-Source Voltage Vs. Typical Gate Charge

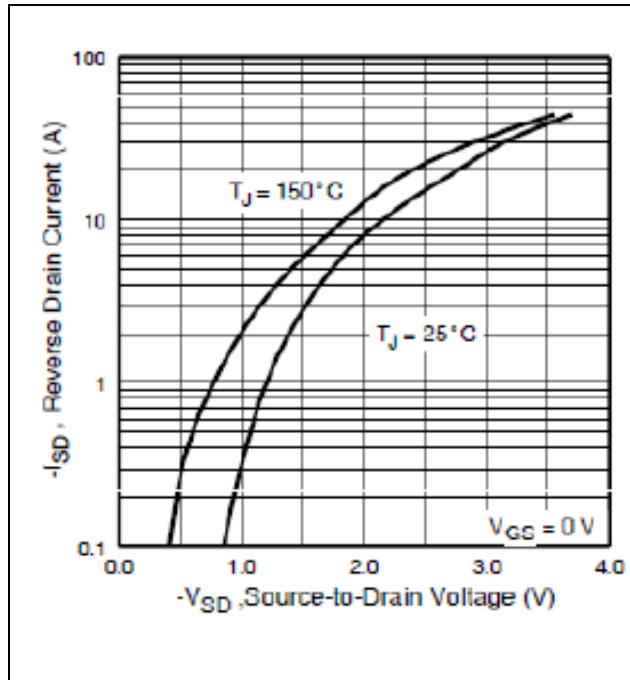


Figure 8 Typical Source-Drain Current Vs. Diode Forward Voltage

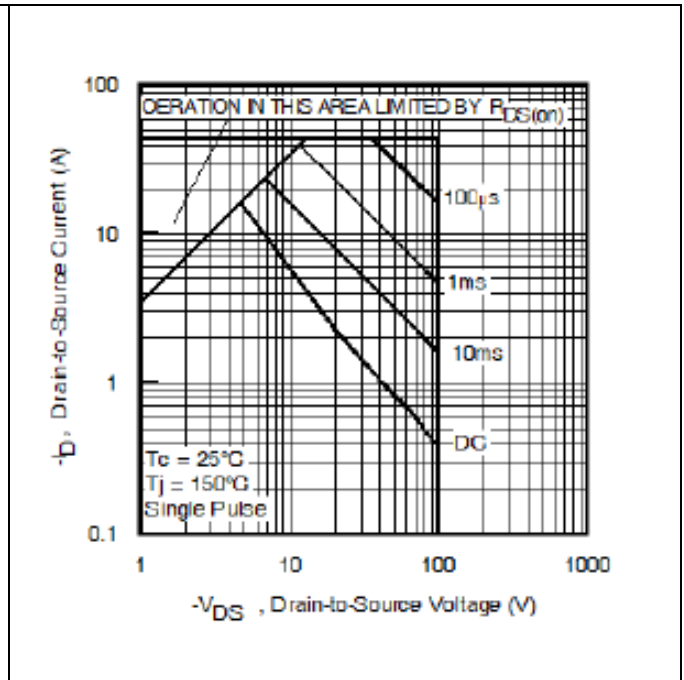


Figure 9 Maximum Safe Operating Area

IRHNJ9130 (JANSR2N7382U3)

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Electrical Characteristics Curves (Pre-irradiation)

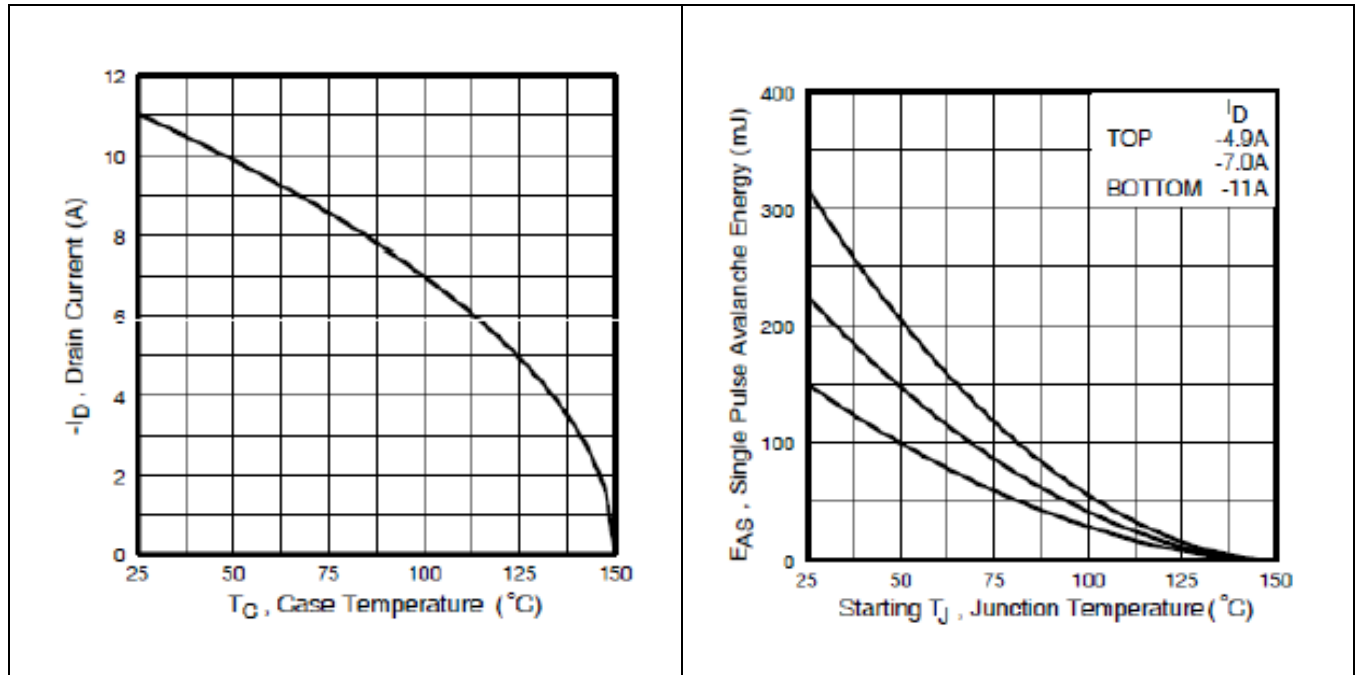


Figure 10 Maximum Drain Current Vs. Case Temperature

Figure 11 Maximum Avalanche Energy Vs. Junction Temperature

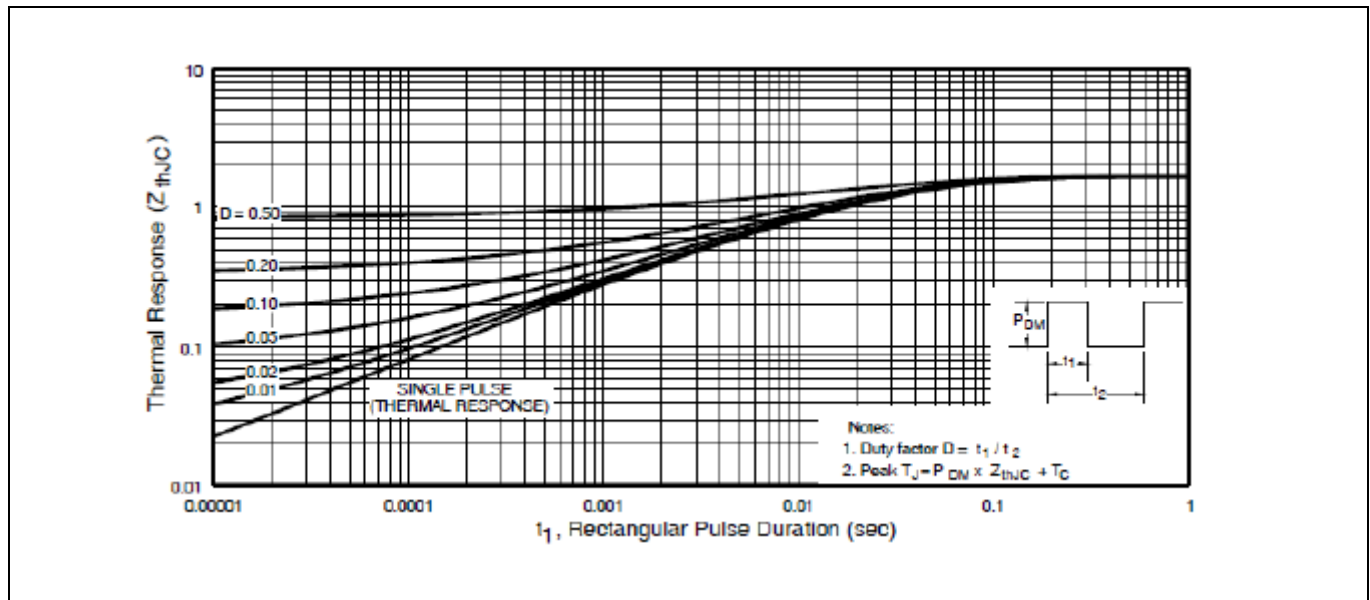


Figure 12 Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRHNJ9130 (JANSR2N7382U3)

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Test Circuits (Pre-irradiation)

4 Test Circuits (Pre-irradiation)

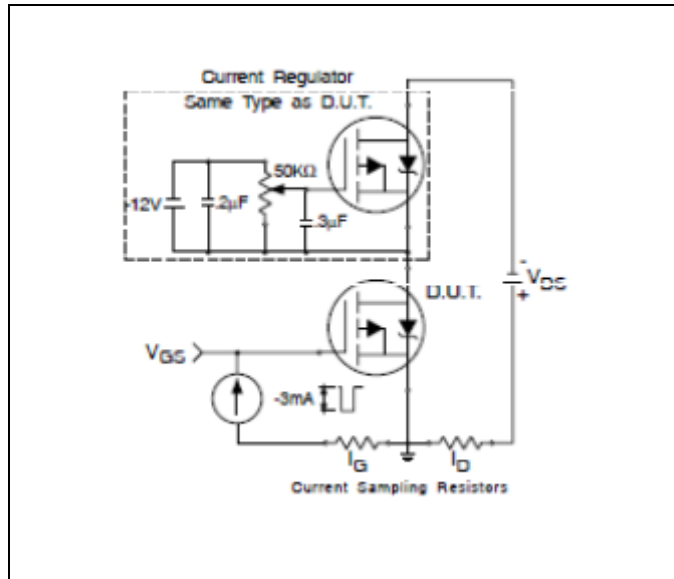


Figure 13 Gate Charge Test Circuit

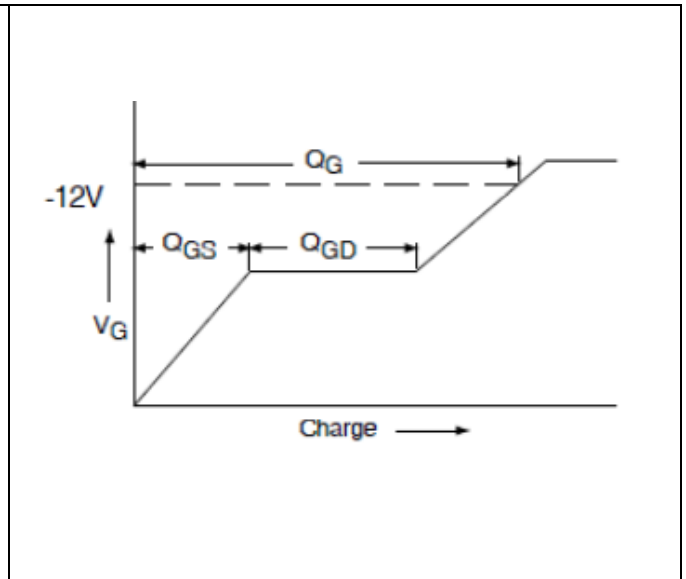


Figure 14 Gate Charge Waveform

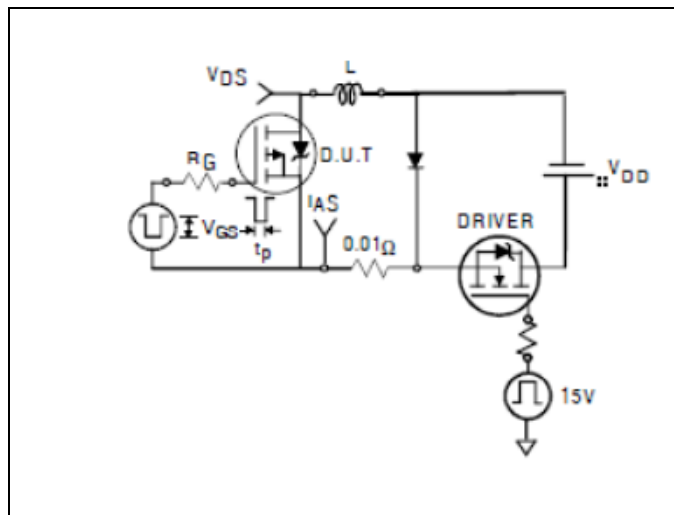


Figure 15 Unclamped Inductive Test Circuit

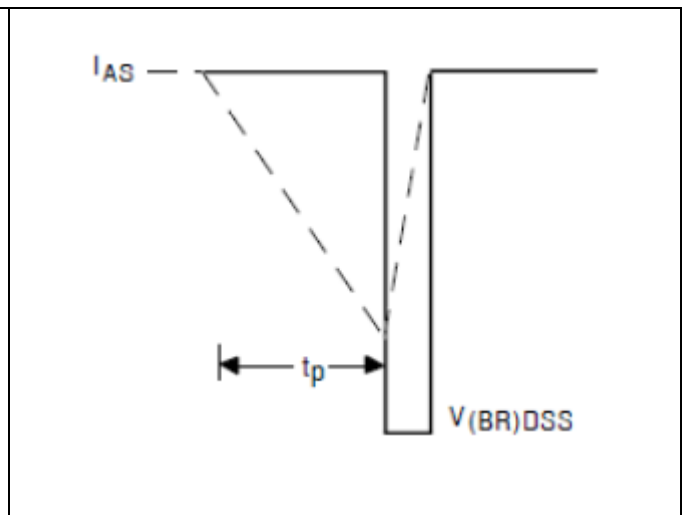


Figure 16 Unclamped Inductive Waveform

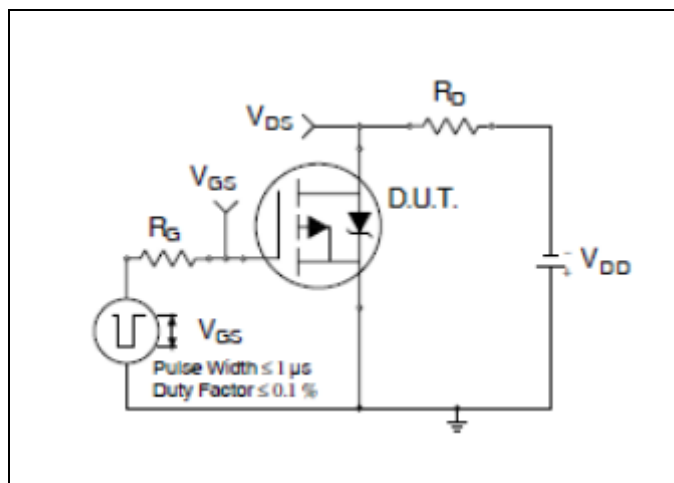


Figure 17 Switching Time Test Circuit

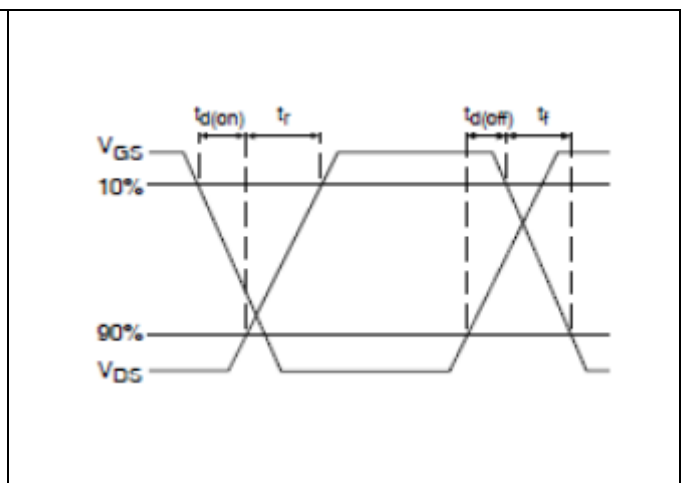
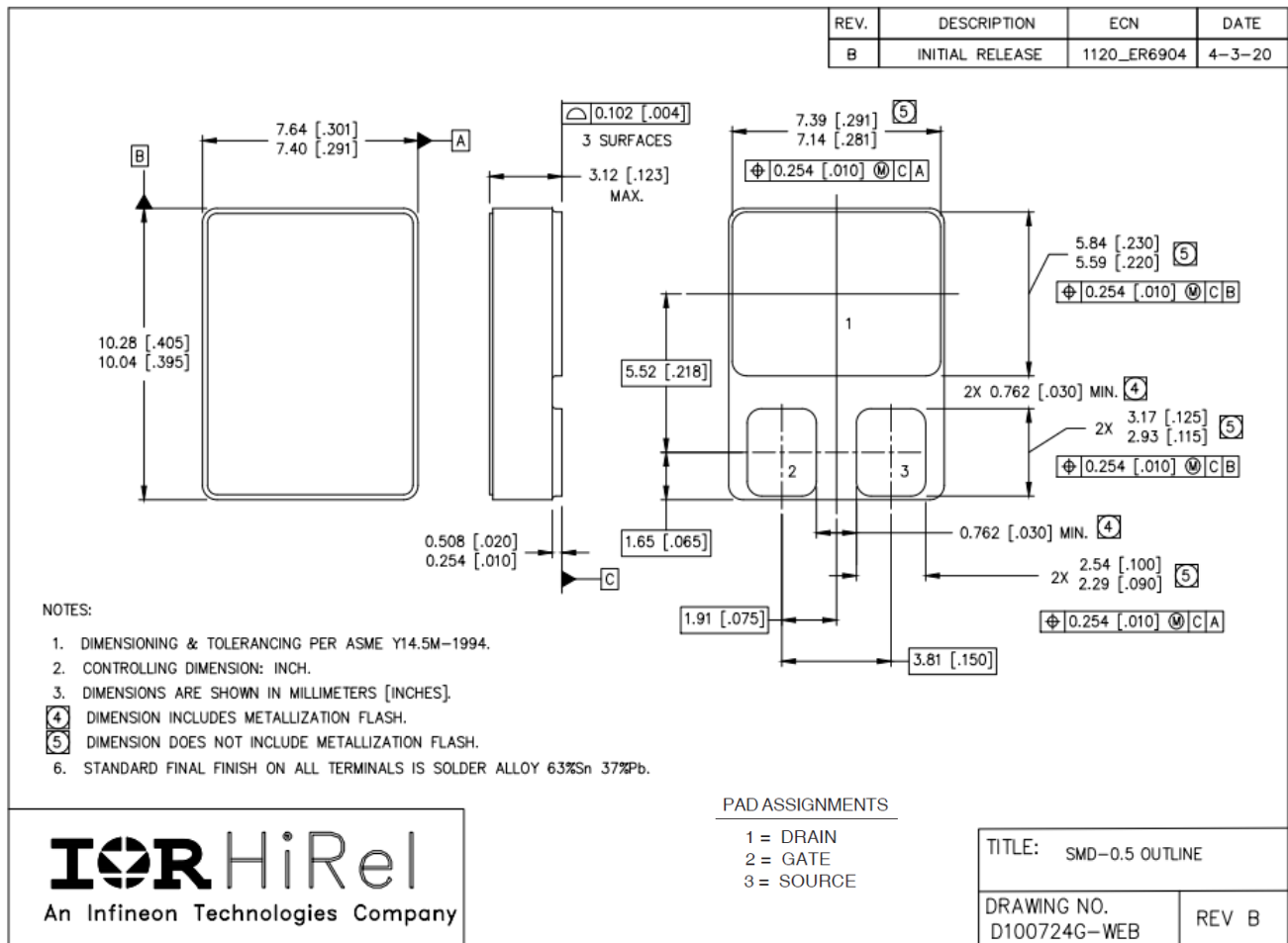


Figure 18 Switching Time Waveforms

Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: [SMD-0.5](#)



Revision history**Revision history**

Document version	Date of release	Description of changes
	07/13/2001	Datasheet (PD-94277)
Rev A	05/20/2006	Updated based on ECN-1120_07667-2
Rev B	05/23/2022	Updated based on ECN-1120_09107

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